

**Notice of References Cited**

Application/Control No.

10/550,855

Applicant(s)/Patent Under  
Reexamination  
VON KAENEL, HANS

Examiner

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Art Unit

2813

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**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
	C	US-			
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**FOREIGN PATENT DOCUMENTS**

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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Rosenblad et al., "Low-temperature heteroepitaxy by LEPECVD", Thin Solid Films 318 (1998) pp. 11-14.
	V	Rosenblad et al., "Epitaxial growth at high rates with LEPECVD", Thin Solid Films 336 (1998) pp. 89-91.
	W	Hackbarth et al., "Alternatives to thick MBE-grown relaxed SiGe buffers", Thin Solid Films 369 (2000) pp. 148-151.
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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